

CD4007M/CD4007C Dual Complementary Pair Plus Inverter

General Description

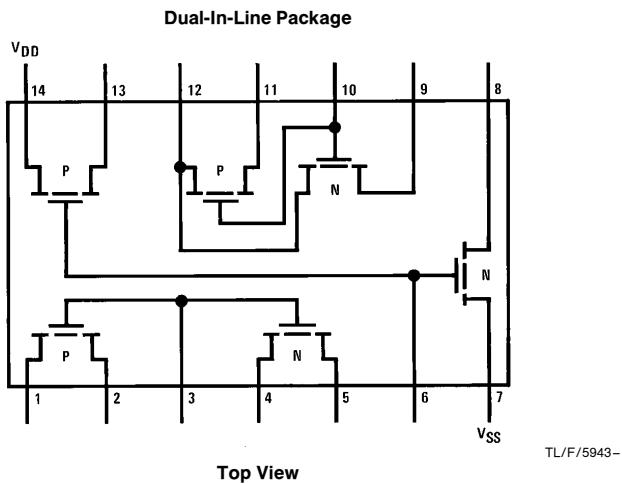
The CD4007M/CD4007C consists of three complementary pairs of N- and P-channel enhancement mode MOS transistors suitable for series/shunt applications. All inputs are protected from static discharge by diode clamps to V_{DD} and V_{SS} .

For proper operation the voltages at all pins must be constrained to be between $V_{SS} - 0.3V$ and $V_{DD} + 0.3V$ at all times.

Features

- Wide supply voltage range 3.0V to 15V
- High noise immunity 0.45 V_{CC} (typ.)

Connection Diagram



Note: All P-channel substrates are connected to V_{DD}
and all N-channel substrates are connected to V_{SS} .

Order Number CD4007

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Voltage at Any Pin $V_{SS} - 0.3V$ to $V_{DD} + 0.3V$

Operating Temperature Range

CD4007M -55°C to $+125^{\circ}\text{C}$
CD4007C -40°C to $+85^{\circ}\text{C}$

Storage Temperature Range -65°C to $+150^{\circ}\text{C}$

Power Dissipation (P_D)

Dual-In-Line 700 mW
Small Outline 500 mW

Operating V_{DD} Range $V_{SS} + 3.0\text{V}$ to $V_{SS} + 15\text{V}$

Lead Temperature (Soldering, 10 seconds) 260°C

DC Electrical Characteristics CD4007M

Symbol	Parameter	Conditions	Limits									Units	
			-55°C			+ 25°C			+ 125°C				
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
I_L	Quiescent Device Current	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$			0.05 0.1		0.001 0.001	0.05 0.1			3.0 6.0	μA μA	
P_D	Quiescent Device Dissipation Package	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$			0.25 1.0		0.005 0.001	0.25 1.0			15 60	μW μW	
V_{OL}	Output Voltage Low Level	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$			0.05 0.05		0 0	0.05 0.05			0.05 0.05	V V	
V_{OH}	Output Voltage High Level	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$	4.95 9.95			4.95 9.95	5.0 10		4.95 9.95			V V	
V_{NL}	Noise Immunity (All Inputs)	$V_{DD} = 5.0\text{V}$, $V_O = 3.6\text{V}$ $V_{DD} = 10\text{V}$, $V_O = 7.2\text{V}$			1.5 3.0		2.25 4.5	1.5 3.0			1.4 2.9	V V	
V_{NH}	Noise Immunity (All Inputs)	$V_{DD} = 5.0\text{V}$, $V_O = 0.95\text{V}$ $V_{DD} = 10\text{V}$, $V_O = 2.9\text{V}$	3.6 7.1			3.5 7.0	2.25 4.5		3.5 7.0			V V	
I_{DN}	Output Drive Current N-Channel	$V_{DD} = 5.0\text{V}$, $V_O = 0.4\text{V}$, $V_I = V_{DD}$ $V_{DD} = 10\text{V}$, $V_O = 0.5\text{V}$, $V_I = V_{DD}$	0.75 1.6			0.6 1.3	1.0 2.5		0.4 0.95			mA mA	
I_{DP}	Output Drive Current P-Channel	$V_{DD} = 5.0\text{V}$, $V_O = 2.5\text{V}$, $V_I = V_{SS}$ $V_{DD} = 10\text{V}$, $V_O = 9.5\text{V}$, $V_I = V_{SS}$	-1.75 -1.35			-1.4 -1.1	-4.0 -2.5		-1.0 -0.75			mA mA	
I_I	Input Current						10					pA	

DC Electrical Characteristics CD4007C

Symbol	Parameter	Conditions	Limits									Units	
			-40°C			+ 25°C			+ 85°C				
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
I_L	Quiescent Device Current	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$			0.5 1.0		0.005 0.005	0.05 1.0			15 30	μA μA	
P_D	Quiescent Device Dissipation Package	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$			2.5 10		0.025 0.05	2.5 10			75 300	μW μW	
V_{OL}	Output Voltage Low Level	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$			0.05 0.05		0 0	0.01 0.01			0.05 0.05	V V	
V_{OH}	Output Voltage High Level	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$	4.95 9.95			4.95 9.95	5.0 10		4.95 9.95			V V	
V_{NL}	Noise Immunity (All inputs)	$V_{DD} = 5.0\text{V}$, $V_O = 3.6\text{V}$ $V_{DD} = 10\text{V}$, $V_O = 7.2\text{V}$			1.5 3.0		2.25 4.5	1.5 3.0			1.4 2.9	V V	
V_{NH}	Noise Immunity (All Inputs)	$V_{DD} = 5.0\text{V}$, $V_O = 0.95\text{V}$ $V_{DD} = 10\text{V}$, $V_O = 2.9\text{V}$	3.6 7.1			3.5 7.0	2.25 4.5		3.5 7.0			V V	
I_{DN}	Output Drive Current N-Channel	$V_{DD} = 5.0\text{V}$, $V_O = 0.4\text{V}$, $V_I = V_{DD}$ $V_{DD} = 10\text{V}$, $V_O = 0.5\text{V}$, $V_I = V_{DD}$	0.35 1.2			0.3 1.0	1.0 2.5		0.24 0.8			mA mA	
I_{DP}	Output Drive Current P-Channel	$V_{DD} = 5.0\text{V}$, $V_O = 2.5\text{V}$, $V_I = V_{SS}$ $V_{DD} = 10\text{V}$, $V_O = 9.5\text{V}$, $V_I = V_{SS}$	-1.3 -0.65			-1.1 -0.55	-4.0 -2.5		-0.9 -0.45			mA mA	
I_I	Input Current						10					pA	

Note 1: This device should not be connected to circuits with the power on because high transient voltages may cause permanent damage.

AC Electrical Characteristics* CD4007M

$T_A = 25^\circ\text{C}$ and $C_L = 15 \text{ pF}$ and rise and fall times = 20 ns. Typical temperature coefficient for all values of $V_{DD} = 0.3\%/\text{ }^\circ\text{C}$

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$t_{PLH} = t_{PHL}$	Propagation Delay Time	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$		35 20	60 40	ns ns
$t_{TLH} = t_{THL}$	Transition Time	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$		50 30	75 40	ns ns
C_I	Input Capacitance	Any Input		5.0		pF

*AC Parameters may be generated by DC correlated testing.

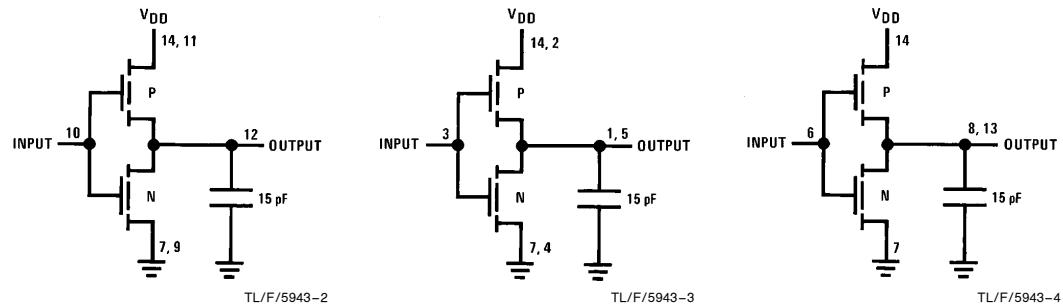
AC Electrical Characteristics* CD4007C

$T_A = 25^\circ\text{C}$ and $C_L = 15 \text{ pF}$ and rise and fall times = 20 ns. Typical temperature coefficient for all values of $V_{DD} = 0.3\%/\text{ }^\circ\text{C}$

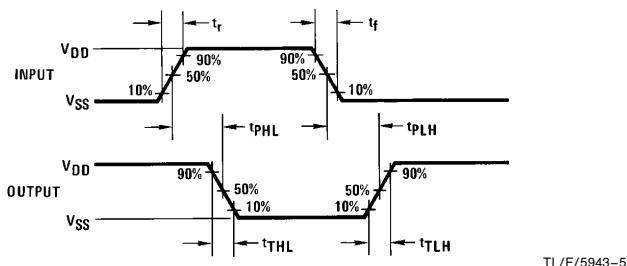
Symbol	Parameter	Conditions	Min	Typ	Max	Units
$t_{PLH} = t_{PHL}$	Propagation Delay Time	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$		35 20	75 50	ns ns
$t_{TLH} = t_{THL}$	Transition Time	$V_{DD} = 5.0\text{V}$ $V_{DD} = 10\text{V}$		50 30	100 50	ns ns
C_I	Input Capacitance	Any Input		5		pF

*AC Parameters are guaranteed by DC correlated testing.

AC Test Circuits

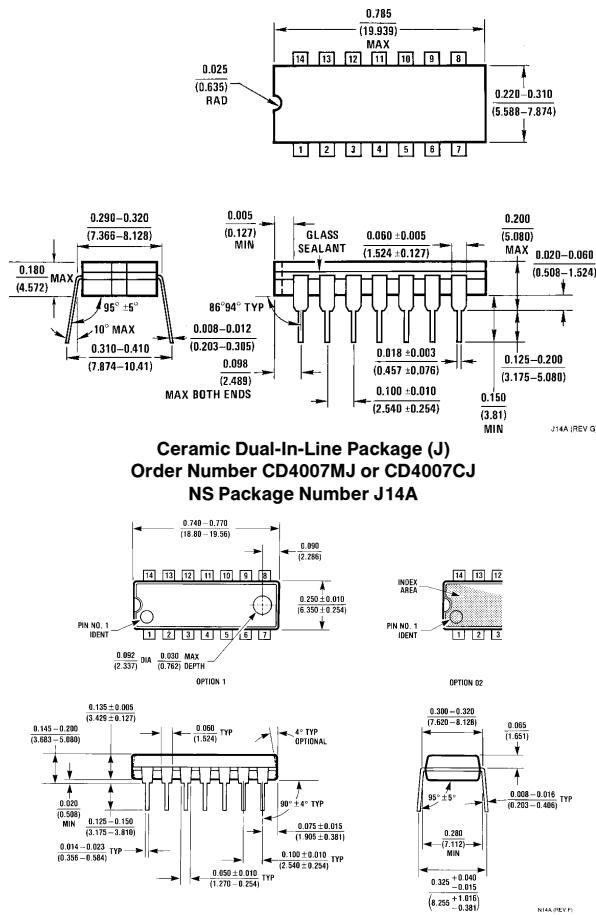


Switching Time Waveforms



CD4007M/CD4007C Dual Complementary Pair Plus Inverter

Physical Dimensions inches (millimeters)



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